	Hits	Search Text	DBs
1	8	(("6720217") or ("6274418") or ("6472752") or ("6642110") or ("6759299") or ("20020197777") or ("20040014269") or ("6159795") or ("2003003660")).PN.	US-PGPUB; USPAT
2	3	(("5696019") or ("6153494") or ("6436765")).PN.	US-PGPUB; USPAT
3	37	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell near5 trench) and (periph$5 near5 trench) and ((cell near5 (region or area)) same (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	3	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell near5 trench) and (periph$5 near5 trench) and ((cell near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4) same amorph$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	3	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell$2 near9 trench$3) and (periph$5 near9 trench$3) and ((cell$2 near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4) same amorph$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	3	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell$2 near9 trench$3) and (periph$5 near9 trench$3) and ((cell$2 near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and (cell same (pad near6 oxide) same thick$6 same (pad near6 nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	9	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell$2 near9 trench$3) and (periph$5 near9 trench$3) and ((cell$2 near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and (cell same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	3	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell near5 trench) and (periph$5 near5 trench) and (((cell or array) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4) same amorph$7)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	9	(flash near5 memory) and cell and periph$5 and gate and source and drain and contact and (cell$2 near9 trench$3) and (periph$5 near9 trench$3) and (((memory or array or cell$2) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and ((cell or memory or array or Rmemo) same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	9	(flash near5 memory) and (cell or memory or array) and periph$5 and gate and source and drain and contact and ((cell$2 or memory or array or Rmemo) near9 (STI or trench$3)) and (periph$5 near9 (STI or trench$3)) and (((memory or array or cell$2) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and ((cell or memory or array or Rmemo) same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
11	13	(flash near5 memory) and (cell or memory or array) and periph$5 and gate and source and drain and ((cell$2 or memory or array or Rmemo) near9 (STI or trench$3)) and (periph$5 near9 (STI or trench$3)) and (((memory or array or cell$2) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and ((cell or memory or array or Rmemo) same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	123	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	140	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3 or deep$4) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	94	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3 or deep$4) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) near9 (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	34	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallower or larger or narrower or deeper) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) near9 (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
16	31	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallower or larger or narrower or deeper or steeper) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4) same substrate same surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	4	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallower or larger or narrower or deeper or steeper) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same ((dop$4 or (ion near5 implant$5) or implant$4) near9 substrate near9 surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
18	1	430/313.ccls. and (((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3 or deep$4) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	1	430/313.ccls. and (cell or memory or array) and periph$5 and gate and source and drain and contact and ((cell$2 or memory or array or Rmemo) near9 (STI or trench$3)) and (periph$5 near9 (STI or trench$3)) and (((memory or array or cell$2) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and ((cell or memory or array or Rmemo) same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
20	1	430/311.ccls. and (((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3 or deep$4) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	1	"430"/$.ccls. and (cell or memory or array) and periph$5 and gate and source and drain and contact and ((cell$2 or memory or array or Rmemo) near9 (STI or trench$3)) and (periph$5 near9 (STI or trench$3)) and (((memory or array or cell$2) near7 (region or area or transistor or memory)) same (dop$4 or (ion near5 implant$5) or implant$4)) and ((cell or memory or array or Rmemo) same (pad near6 oxide) same (pad near6 nitride) same perip$7) and ((photoresist or resist) same pattern$4 same etch$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	148	(((cell or memory or array or Rmemo) near9 (trench$3 or STI)) same (shallow$3 or large$3 or narrow$3 or deep$4) same ((Rperiph$6 or periph$5) near9 (trench$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (dop$4 or (ion near5 implant$5) or implant$4 or (diffusion near5 region)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB